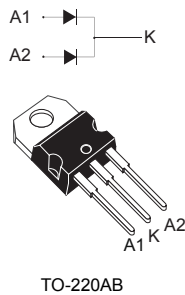


100 V, 40 A power Schottky rectifier



Features

- Low forward voltage drop
- Good trade-off between leakage current and forward voltage drop
- High frequency operation
- Avalanche capability specified
- ECOPACK[®]2 compliant

Applications

- Switching diode
- SMPS
- DC/DC converter
- LED lighting
- Adapter for notebook and game station

Description

The **STPS40SM100C** is suited for high frequency switch mode power supply.

Packaged in TO-220AB, the **STPS40SM100C** is optimized for use in notebook and game station adaptors, providing in these applications a good efficiency at both low and high load.

Product status link

[STPS40SM100C](#)

Product summary

Symbol	Value
$I_{F(AV)}$	2 x 20 A
V_{RRM}	100 V
T_j (max.)	150 °C
V_F (typ.)	0.605 V

1 Characteristics

Table 1. Absolute Ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit	
V _{RRM}	Repetitive peak reverse voltage		100	V	
I _{F(RMS)}	Forward rms current		60	A	
I _{F(AV)}	Average forward current, $\delta = 0.5$ square wave	T _C = 130 °C	Per diode	20	A
		T _C = 125 °C	Per device	40	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	350	A	
P _{ARM}	Repetitive peak avalanche power	t _p = 10 μ s, T _j = 125 °C	1295	W	
T _{stg}	Storage temperature range		-65 to +175	°C	
T _j	Maximum operating junction temperature ⁽¹⁾		150	°C	

1. $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter	Max. value	Unit
R _{th(j-c)}	Junction to case	Per diode	1.3
		Total	0.7
R _{th(c)}	Coupling	0.1	°C/W

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode1}) = P_{(\text{diode1})} \times R_{th(j-c)} (\text{per diode}) + P_{(\text{diode2})} \times R_{th(c)}$$

For more information, please refer to the following application note :

- AN5088 : Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = 70 V	-	7		μ A
		T _j = 125 °C		-	7		mA
		T _j = 25 °C	V _R = 100 V	-	13	45	μ A
		T _j = 125 °C		-	13	45	mA
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 5 A	-	520		mV
		T _j = 125 °C		-	435		
		T _j = 25 °C	I _F = 10 A	-	620	700	
		T _j = 125 °C		-	520	580	
		T _j = 25 °C	I _F = 20 A	-	740	810	
		T _j = 125 °C		-	605	665	

1. Pulse test: t_p = 5 ms, $\delta < 2\%$

2. Pulse test: t_p = 380 μ s, $\delta < 2\%$

To evaluate the conduction losses, use the following equation: $P = 0.580 \times I_{F(AV)} + 0.0043 \times I_F^2 (RMS)$

For more information, please refer to the following application notes related to the power losses :

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (per diode)

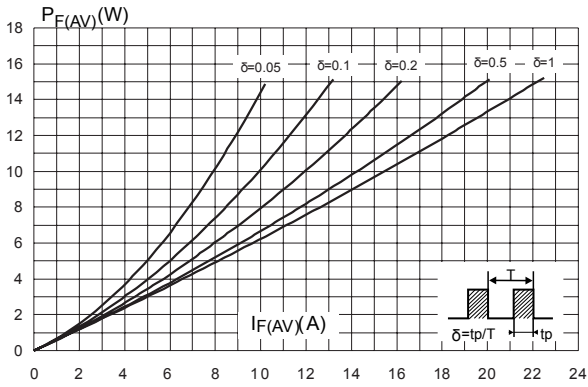


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

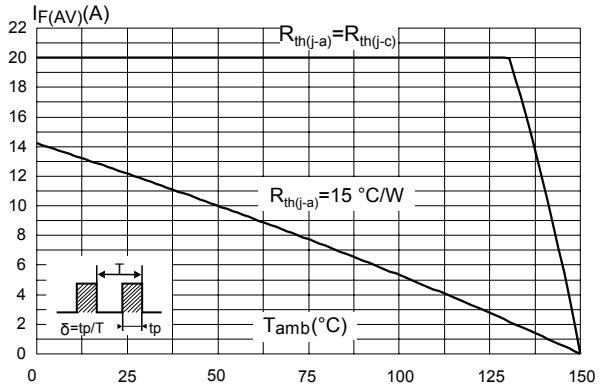


Figure 3. Normalized avalanche power derating versus pulse duration ($T_j = 125^\circ\text{C}$)

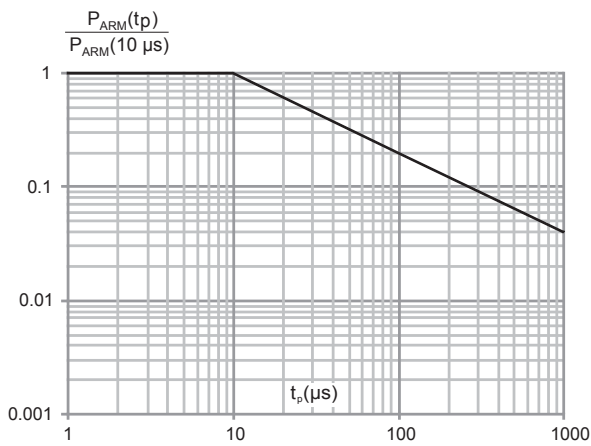


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

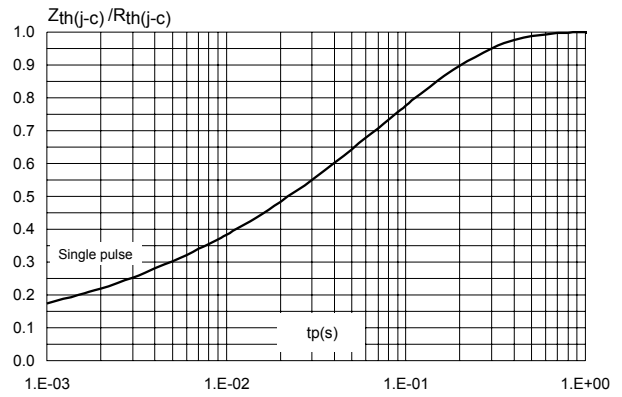


Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

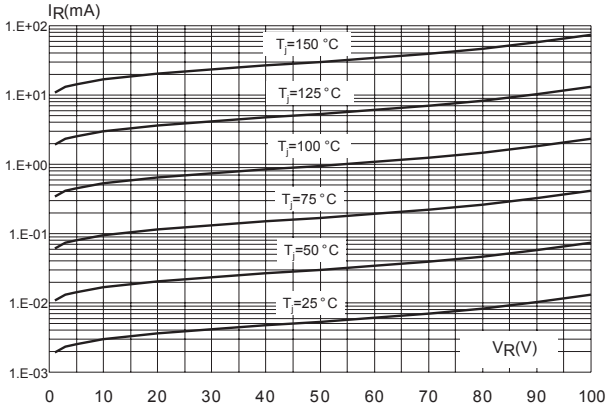


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

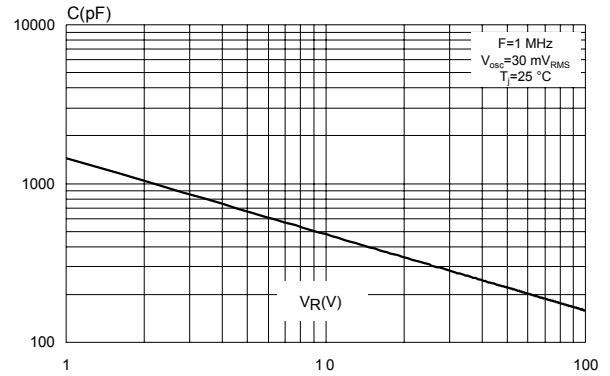
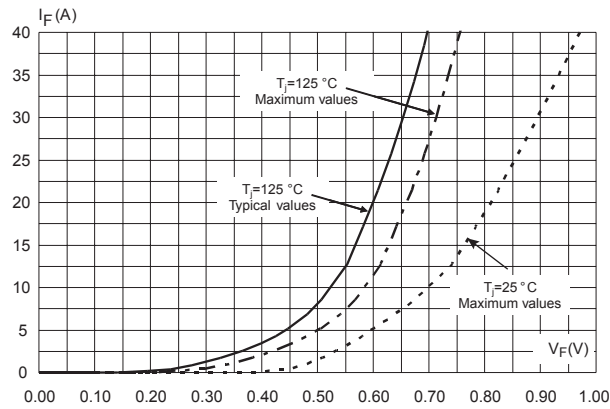


Figure 7. Forward voltage drop versus forward current (per diode)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-220AB package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 8. TO-220AB package outline

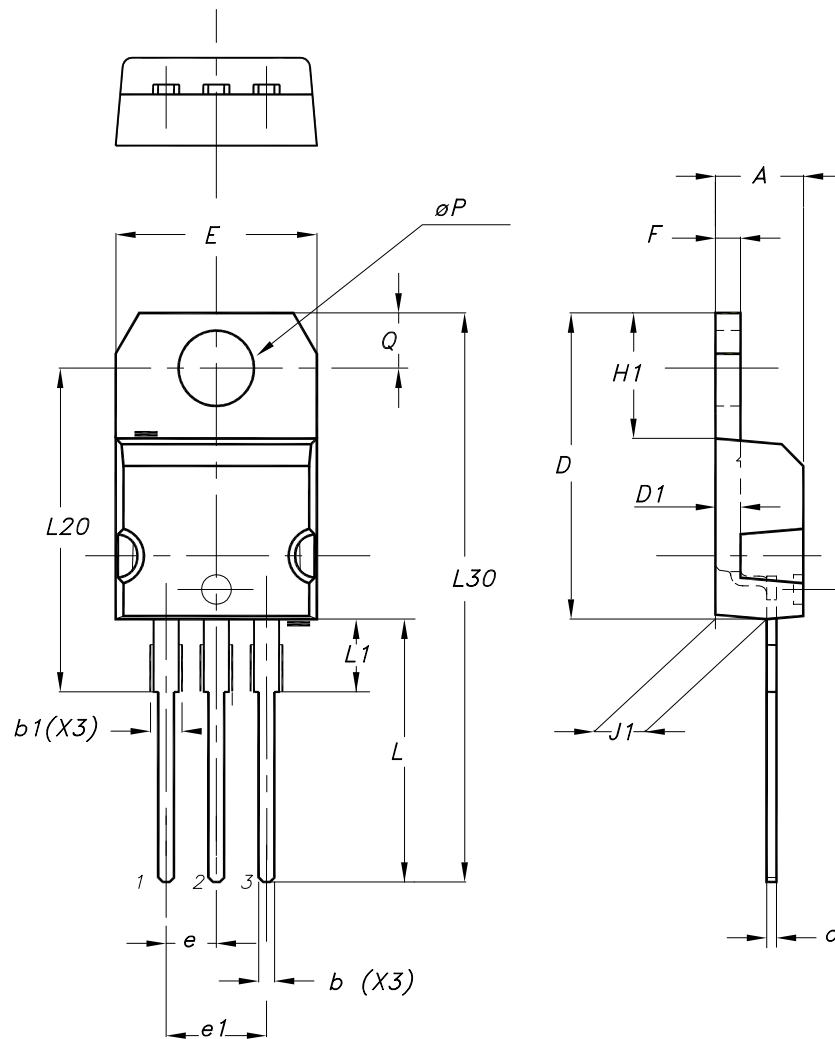


Table 4. TO-220AB package mechanical data

Ref.	Dimensions			
	Millimeters		Inches (for reference only)	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
b	0.61	0.88	0.240	0.035
b1	1.14	1.55	0.045	0.061
c	0.48	0.70	0.019	0.028
D	15.25	15.75	0.600	0.620
D1	1.27 typ.		0.050 typ.	
E	10.00	10.40	0.394	0.409
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.244	0.260
J1	2.40	2.72	0.094	0.107
L	13.00	14.00	0.512	0.551
L1	3.50	3.93	0.138	0.155
L20	16.40 typ.		0.646 typ.	
L30	28.90 typ.		1.138 typ.	
θP	3.75	3.85	0.148	0.152
Q	2.65	2.95	0.104	0.116

3 Ordering information

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS40SM100CT	PS40SM100CT	TO-220AB	1.95 g	50	Tube

Revision history

Table 6. Document revision history

Date	Version	Changes
25-Mar-2009	1	First issue.
15-Apr-2010	2	Updated package graphics for TO-220AB on front page and in Table 5
27-Jun-2018	3	Updated Table 1. Absolute Ratings (limiting values, per diode, at 25 °C, unless otherwise specified) and Figure 3. Normalized avalanche power derating versus pulse duration ($T_j = 125\text{ °C}$). Removed I ² PAK and D ² PAK package information.
22-Feb-2019	4	Updated Table 1.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2019 STMicroelectronics – All rights reserved

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9